

[placing a substrate in a reaction chamber; introducing a first reactive gas comprising a carbon free material; activating said first reactive gas by supplying energy thereto; depositing a first layer on said substrate; introducing a second reactive gas into said reaction chamber after depositing said first layer, said second reactive gas in order to convert said gas to a plasma; and

depositing a silicon oxide film on said first layer]
forming a first layer comprising silicon oxide on a substrate by CVD
using a first reactive gas comprising a carbon free silicon containing
material; and
forming a second layer comprising silicon oxide on said first layer
by CVD using a second reactive gas comprising at least TEOS.

8. (Amended) The method of claim 7 wherein [said first layer comprises a silicon oxide] said second layer is formed by plasma CVD.

Please add the following new claims:

--11. A method of forming a film on a substrate comprising the steps of:

placing a substrate in a reaction chamber, said substrate having a plurality of leads formed thereon;

introducing a reactive gas comprising at least TEOS into said reaction chamber;

supplying energy into said reaction chamber; and
forming a silicon oxide layer on said substrate.

12. The method of claim 11 wherein said leads comprises aluminum.

13. The method of claim 11 wherein said leads are about 0.8 μm in height, about 0.6 μm in width and a gap between each lead is about 0.9 μm .

14. The method of claim 11 further comprising the step of forming a buffer layer between said substrate and said silicon oxide layer.

15. A method of forming a film having a uniform thickness on an uneven surface of a substrate comprising the steps of:

placing said substrate in a reaction chamber;
introducing a reactive gas comprising at least TEOS;
supplying energy to said reactive gas in order to activate said gas;
and

depositing a film on said substrate by CVD wherein said TEOS is in a liquid state during deposition.--

REMARKS

Claims 1-6 have been cancelled without prejudice or disclaimer of the subject matter contained therein, and claims 7 and 8 have been amended to more clearly recite the present invention. Further, new claims 11-15 have been added. It is respectfully requested that pending claims 7-15 be considered allowable and the application passed to issue.